N-Channel Enhancement Mode MOSFET

BSS138BKW

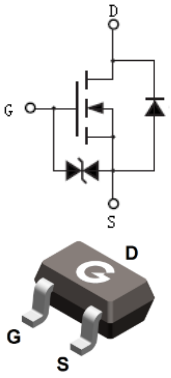
Features

- Fast switching speed
- HBM: JESD22-A114-B: 2
- RoHS compliant with Halogen-free

HF

Mechanical Data

- Case: SOT-323
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



SOT-323

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BSS138BKW	SOT-323	3000 pcs / Tape & Reel	138BK

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	60	V
Gate-to-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current (T_A = 25°C) *1	I_D	450	mA
Continuous Drain Current (T_A = 70°C) *1		360	mA
Pulsed Drain Current (t_p = 10μs, T_A = 25°C)	I_{DM}	1800	mA
Power Dissipation (T_A = 25°C) *1	P_D	300	mW
Operating Junction Temperature Range	T_J	-55 ~ +150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	-	-	420	°C/W

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60V, V_{GS} = 0V	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±10	μA
On Characteristics						
$R_{DS(ON)}$	Static Drain-Source On-resistance *2	V_{GS} = 10V, I_D = 0.4A	-	0.56	0.7	Ω
		V_{GS} = 4.5V, I_D = 0.2A	-	0.64	1.2	
		V_{GS} = 2.5V, I_D = 0.1A	-	0.92	3	
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	0.8	1.0	1.5	V
R_G	Gate Resistance	V_{GS} = 0V, f = 1MHz	-	42	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{GS} = 0V V_{DS} = 30V f = 1.0MHz	-	65	-	pF
C_{OSS}	Output Capacitance		-	12	-	
C_{RSS}	Reverse Transfer Capacitance		-	7	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time *3	V_{DD} = 30V V_{GS} = 10V I_D = 0.36A R_G = 6Ω	-	2	-	ns
t_r	Turn-on Rise Time *3		-	19	-	
$t_{d(OFF)}$	Turn-Off Delay Time *3		-	6	-	
t_f	Turn-Off Fall Time *3		-	23	-	
Q_G	Total Gate-Charge	V_{DS} = 30V V_{GS} = 4.5V I_D = 0.2A	-	2.3	-	nC
Q_{GS}	Gate to Source Charge		-	0.6	-	
Q_{GD}	Gate to Drain (Miller) Charge		-	0.5	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage *2	I_S = 0.4A, V_{GS} = 0 V	-	0.8	1.4	V

Notes:

1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
3. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

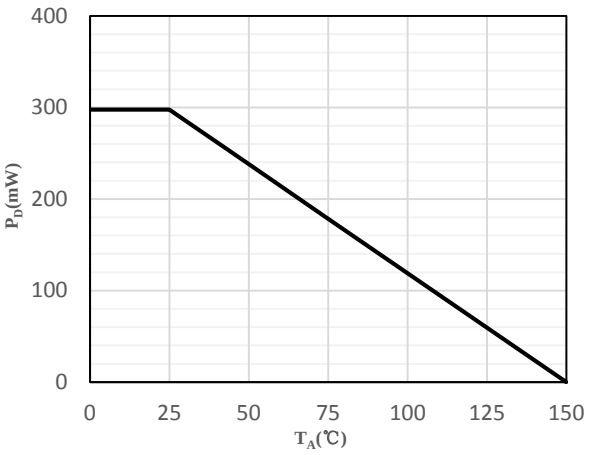


Fig 1 Power Dissipation

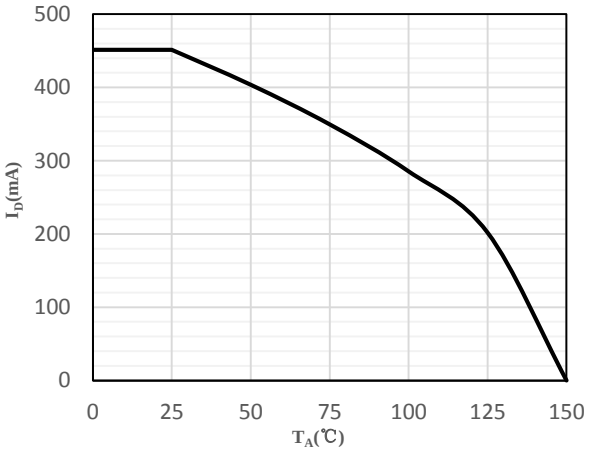


Fig 2 Drain Current

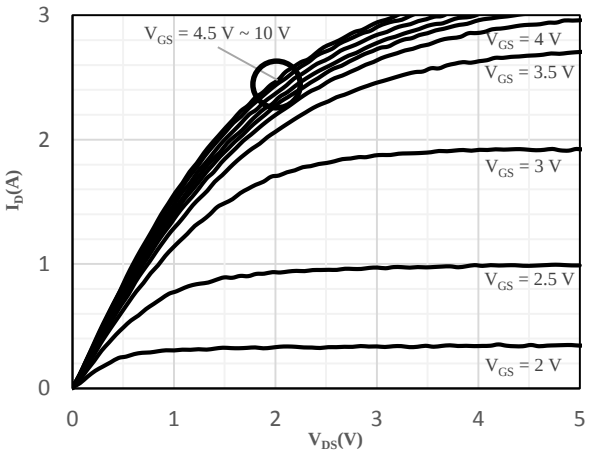


Fig 3 Typical Output Characteristics

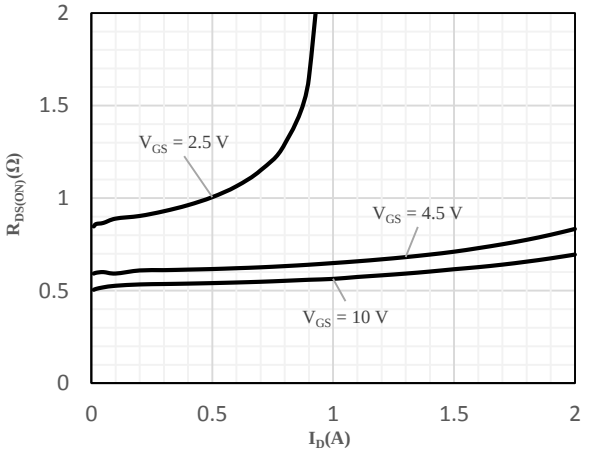


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

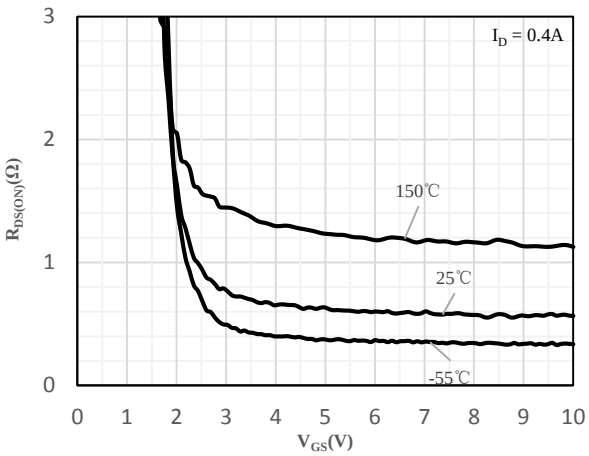


Fig 5 On-Resistance vs. Gate-Source Voltage

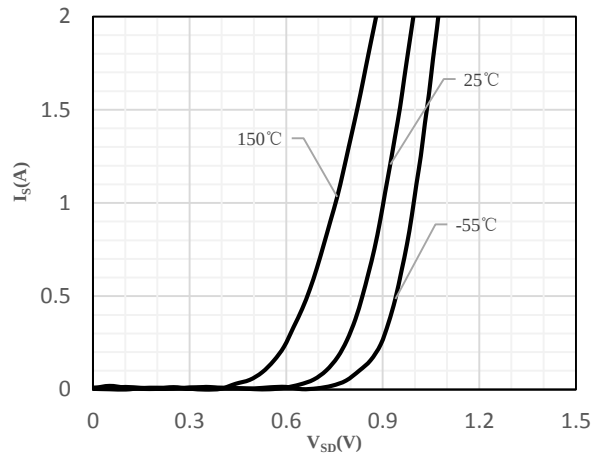


Fig 6 Body-Diode Characteristics

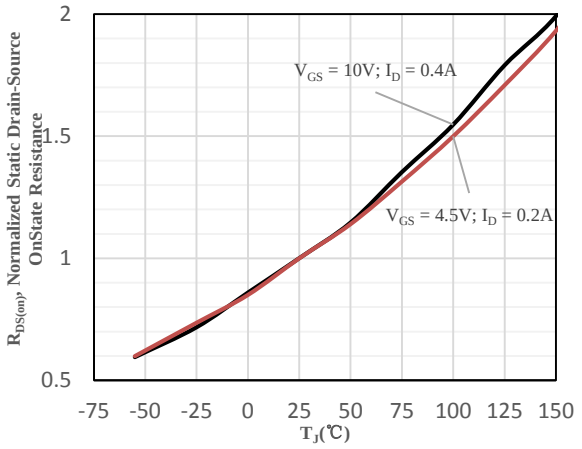


Fig 7 Normalized On-Resistance vs. Junction Temperature

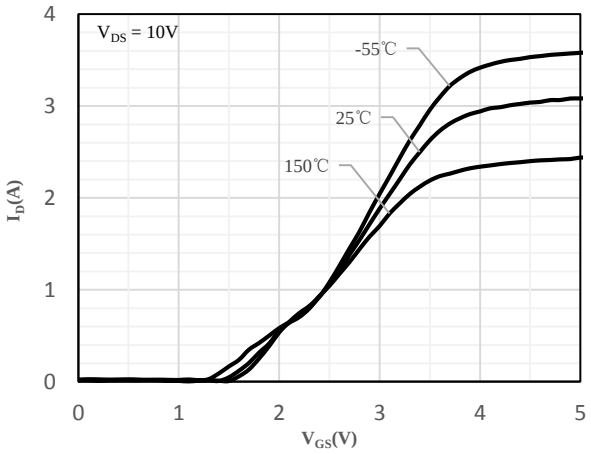


Fig 8 Transfer Characteristics

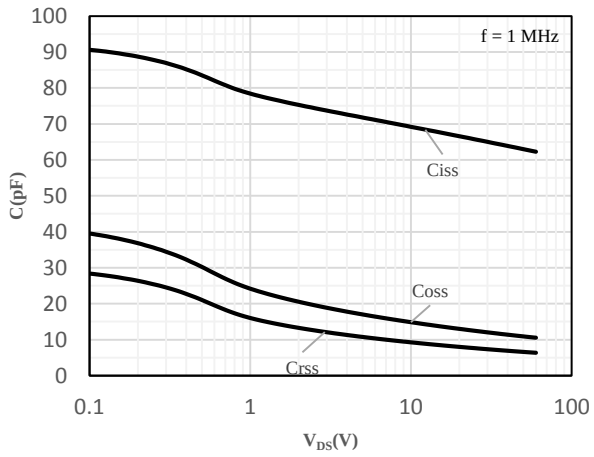


Fig 9 Capacitance Characteristics

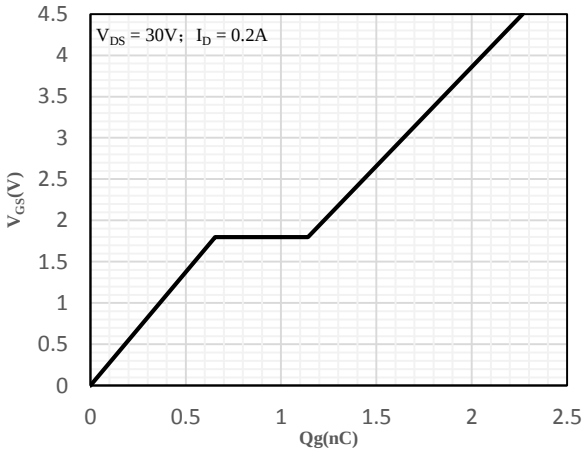


Fig 10 Gate-Charge Characteristics

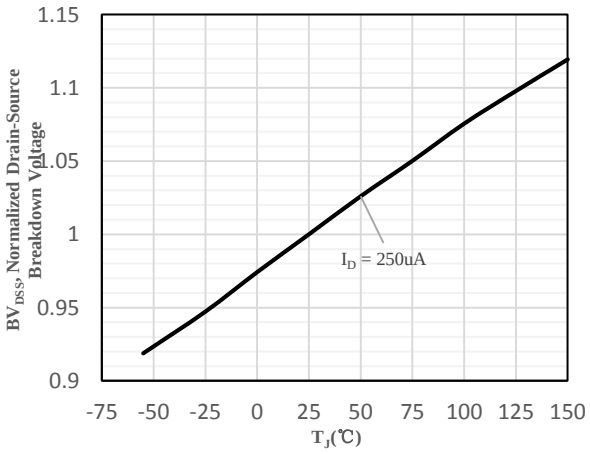


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

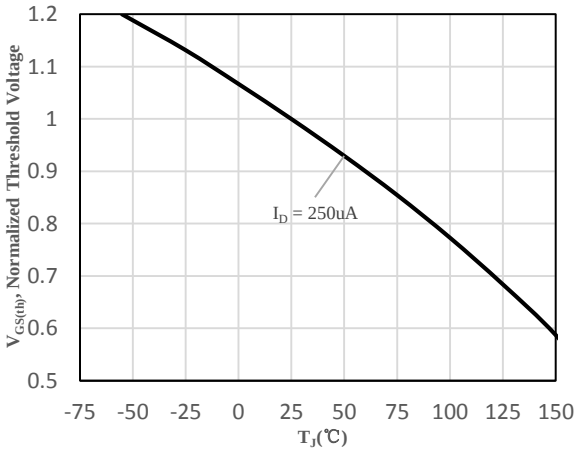
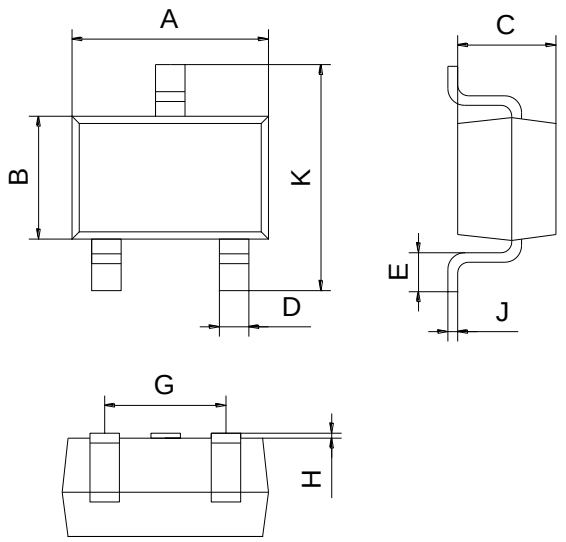


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

Package Outline Dimensions (Unit: mm)



SOT-323		
Dimension	**Min.**	**Max.**
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	0.25	0.40
G	1.20	1.40
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout (Unit: mm)

SOT-323